

New Product

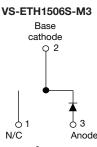
VS-ETH1506S-M3, VS-ETH1506-1-M3

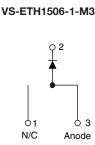
Vishay Semiconductors

Hyperfast Rectifier, 15 A FRED Pt[®]









D²PAK

TO-262

PRODUCT SUMMARY								
Package	TO-263AB (D ² PAK), TO-262AA							
I _{F(AV)}	15 A							
V _R	600 V							
V _F at I _F	2.45 V							
t _{rr} (typ.)	21 ns							
T _J max.	175 °C							
Diode variation	Single die							

FEATURES

- Hyperfast recovery time
- · Low forward voltage drop
- 175 °C operating junction temperature
- Low leakage current
- Compliant to RoHS Directive 2002/95/EC
- Halogen-free according to IEC 61249-2-21 definition



FREE

Designed and gualified according to JEDEC-JESD47

DESCRIPTION/APPLICATIONS

Hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC Boost stage in the AC/DC section of SMPS, inverters or as freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS							
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS			
Repetitive peak reverse voltage	V _{RRM}		600	V			
Average rectified forward current	I _{F(AV)}	T _C = 139 °C	15	٨			
Non-repetitive peak surge current	I _{FSM}	$T_{\rm C} = 25 \ ^{\circ}{\rm C}$	160	A			
Operating junction and storage temperatures	T _J , T _{Stg}		- 65 to 175	°C			

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA	600	-	-			
	V _F	I _F = 15A	-	1.8	2.45	V		
Forward voltage		I _F = 15 A, T _J = 150 °C	-	1.25	1.6			
Povorao lookogo ourront	I _R	V _R = V _R rated	-	0.01	15			
Reverse leakage current		$T_J = 150 \text{ °C}, V_R = V_R \text{ rated}$	-	20	200	μA		
Junction capacitance	CT	V _R = 600 V	-	12	-	pF		
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH		

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DYNAMIC RECOVERY CH	IARACTER	RISTICS ($T_J = 25$	°C unless otherw	vise speci	fied)		
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	100 A/ μ s, V _R = 30 V	-	21	26	
Poverse receiver time	+	I _F = 1.5 A, dI _F /dt =	100 A/µs, V _R = 30 V	-	25	36	ns
Reverse recovery time	t _{rr}	T _J = 25 °C		-	29	-	115
		T _J = 125 °C	I _F = 15 A dI _F /dt = 200 A/μs V _R = 390 V	-	65	-	
Peak recovery current	I _{RRM}	T _J = 25 °C		-	3.9	-	A
Peak recovery current		T _J = 125 °C		-	7.0	-	A
	Q _{rr}	T _J = 25 °C		-	60	-	nC
Reverse recovery charge		T _J = 125 °C		-	240	-	no
Reverse recovery time	t _{rr}		I _F = 15 A	-	42	-	ns
Peak recovery current	I _{RRM}	T _J = 125 °C	dI _F /dt = 800 A/µs	-	21	-	А
Reverse recovery charge	Q _{rr}		V _R = 390 V	-	480	-	nC

THERMAL - MECHANICAL SPECIFICATIONS								
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS		
Maximum junction and storage temperature range	T _J , T _{Stg}		- 65	-	175	°C		
Thermal resistance, junction to case	R _{thJC}		-	1.3	1.51	°C/W		
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	70			
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-			
Woight			-	2.0	-	g		
Weight			-	0.07	-	oz.		
Mounting torque			6 (5)	-	12 (10)	kgf · cm (lbf · in)		
Marking daying		Case style D ² PAK modified	ETH1506S					
Marking device		Case style TO-262		ETH1	506-1			

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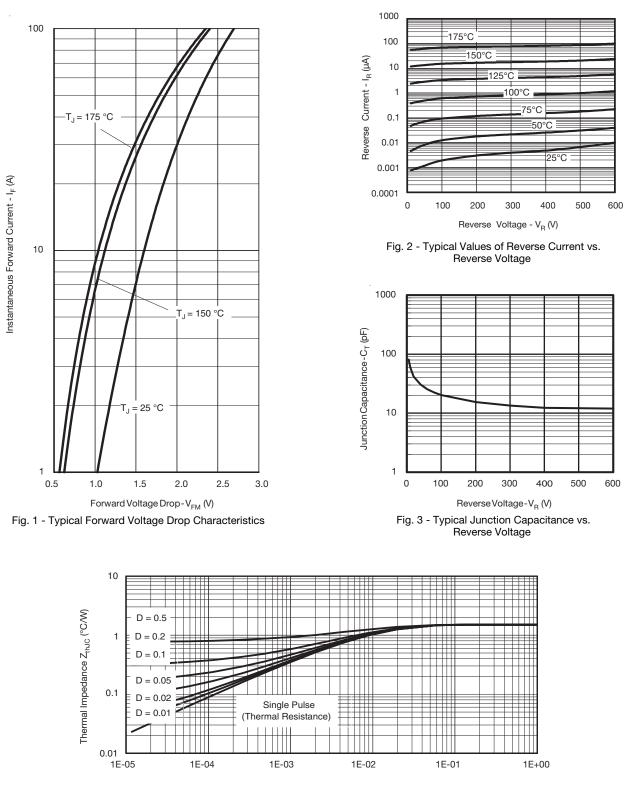
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New Product

VS-ETH1506S-M3, VS-ETH1506-1-M3

Hyperfast Rectifier, 15 A FRED Pt[®] Vishay Semiconductors



t, Rectangular Pulse Duration (s)

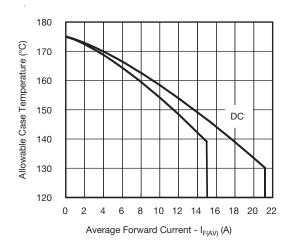
Fig. 4 - Max. Thermal Impedance Z_{thJC} Characteristics

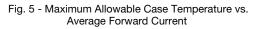
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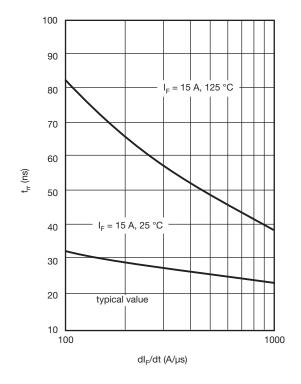


Fig. 7 - Typical Reverse Recovery Time vs. $dI_{\mbox{\scriptsize F}}/dt$

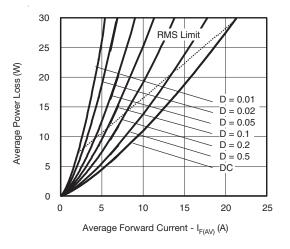


Fig. 6 - Forward Power Loss Characteristics

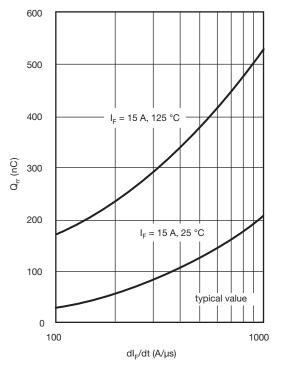


Fig. 8 - Typical Stored Charge vs. dl_F/dt

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Hyperfast Rectifier, 15 A FRED Pt[®] Vishay Semiconductors

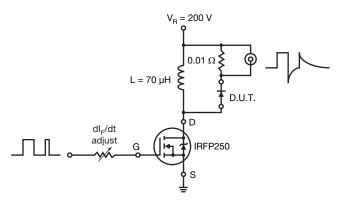


Fig. 9 - Reverse Recovery Parameter Test Circuit

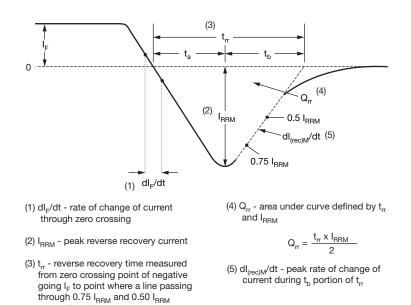


Fig. 10 - Reverse Recovery Waveform and Definitions

extrapolated to zero current.

Vishay Semiconductors Hyperfast Rectifier, 15 A FRED Pt®



ORDERING INFORMATION TABLE

Device code	VS-	Е	т	н	15	06	S	TRL	-M3
	(1)	2	3	4	(5)	6	(7)	8	9
	1 -	Visł	nay Sen	niconduc	ctors pro	oduct			
	2 -			iguratior	n				
	E = Single diode 3 - T = TO-220								
	4 -			ast recov	verv tim	е			
	5 -		• •	le (15 =	-				
	6 -	Volt	age coo	le (06 =	600 V)				
	7 -	• S	= D ² PA	K					
		• -1	= TO-2	62					
	8 -	• No	one = Ti	ube (50	pieces)				
	-	• TF	RL = Tap	be and r	eel (left	oriente	d, for D	² PAK p	ackage
	-	• TF	RR = Ta	pe and i	reel (rigl	ht orient	ted, for	D ² PAK	packag
	9 -	-M3	= Halo	gen-free	e, RoHS	complia	ant, and	d termin	ations I

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-ETH1506S-M3	50	1000	Antistatic plastic tube					
VS-ETH1506-1-M3	50	1000	Antistatic plastic tube					
VS-ETH1506STRR-M3	800	800	13" diameter reel					
VS-ETH1506STRL-M3	800	800	13" diameter reel					

LINKS TO RELATED DOCUMENTS							
Dimensions	TO-263AB (D ² PAK)	www.vishay.com/doc?95046					
	TO-262AA	www.vishay.com/doc?95419					
Dort moreling information	TO-263AB (D ² PAK)	www.vishay.com/doc?95444					
Part marking information	TO-262AA	www.vishay.com/doc?95443					
Packaging information	TO-263AB (D ² PAK)	www.vishay.com/doc?95032					

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Outline Dimensions

Vishay Semiconductors

D²PAK



Conforms to JEDEC outline D²PAK (SMD-220) в Pad layout (2)(3)A 11.00 MIN.-(E) F (0.43)ŧ (3) L1 4 (|(0.38)^{MIN.} (D1) (3) Detail A D 17.90 (0.70) Н 15.00 (0.625) (2) З 0.15)^{0.01} Ľ L2 Ĥ ţ В В 2.32 MIN. (0.08) 2.64 (0.103) 2.41 (0.096) (3)Ċ 2 x b2 С View A - A 2 x h // ± 0.004 M B ⊕ 0.010 M A M B Base Plating (4) Metal 2 x e Н b1, b3 Gauge plane c1 (4) (c) В 0° to 8° ŧ. Seating Lead assignments plane L3 A1 Lead tip (b, b2) Diodes Section B - B and C - C 1. - Anode (two die)/open (one die) Scale: None 2., 4. - Cathode Detail "A" 3. - Anode

Rotated 90 °CW Scale: 8:1

SYMBOL	MILLIMETERS		INCHES		NOTES		SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC	
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625	
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110	
с	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070	
c2	1.14	1.65	0.045	0.065			L3	0.25	BSC	0.010	BSC	
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208	

Notes

 $^{(1)}\,$ Dimensioning and tolerancing per ASME Y14.5 M-1994 $\,$

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

⁽⁵⁾ Datum A and B to be determined at datum plane H

⁽⁶⁾ Controlling dimension: inch

⁽⁷⁾ Outline conforms to JEDEC outline TO-263AB

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DIMENSIONS in millimeters and inches

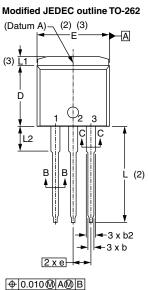


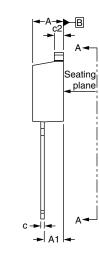
Outline Dimensions

Vishay Semiconductors

TO-262

DIMENSIONS in millimeters and inches

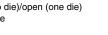


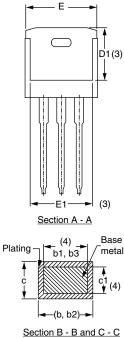


Lead assignments



Diodes 1. - Anode (two die)/open (one die) 2., 4. - Cathode 3. - Anode





Scale: None

SYMBOL	MILLIM	ETERS	INC	NOTES	
	MIN.	MAX.	MIN.	MAX.	NOTES
А	4.06	4.83	0.160	0.190	
A1	2.03	3.02	0.080	0.119	
b	0.51	0.99	0.020	0.039	
b1	0.51	0.89	0.020	0.035	4
b2	1.14	1.78	0.045	0.070	
b3	1.14	1.73	0.045	0.068	4
С	0.38	0.74	0.015	0.029	
c1	0.38	0.58	0.015	0.023	4
c2	1.14	1.65	0.045	0.065	
D	8.51	9.65	0.335	0.380	2
D1	6.86	8.00	0.270	0.315	3
E	9.65	10.67	0.380	0.420	2, 3
E1	7.90	8.80	0.311	0.346	3
е	2.54 BSC		0.100 BSC		
L	13.46	14.10	0.530	0.555	
L1	-	1.65	-	0.065	3
L2	3.56	3.71	0.140	0.146	

Notes

Revision: 04-Oct-10

⁽¹⁾ Dimensioning and tolerancing as per ASME Y14.5M-1994

⁽²⁾ Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

⁽⁴⁾ Dimension b1 and c1 apply to base metal only

(5) Controlling dimension: inches

(6) Outline conform to JEDEC TO-262 except A1 (maximum), b (minimum) and D1 (minimum) where dimensions derived the actual package outline

⁽³⁾ Thermal pad contour optional within dimension E, L1, D1 and E1

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